Silicon NPN Phototransistor

Description

BPW85 is a high speed and high sensitive silicon NPN epitaxial planar phototransistor in a T-1 (Ø 3 mm) clear, plastic package. It is sensitive for visible and near infrared radiation.

Features

- High photo sensitivity
- Options: sensitivity group A, B or C
- Angle of half sensitivity: $\varphi = \pm 25°$
- Fast response times
- Sensitive for visible and near infrared radiation
- Package: T-1 (Ø 3 mm), clear plastic
- Lead (Pb)-free component in accordance with RoHS 2002/95/EC and WEEE 2002/96/EC

Applications

- Detector in electronic control and drive circuits

Parts Table

Part	Ordering code	Remarks
BPW85A	BPW85A	Minimum order quantity: 5000 pcs, 5000 pcs/bulk
BPW85B	BPW85B	Minimum order quantity: 5000 pcs, 5000 pcs/bulk
BPW85C	BPW85C	Minimum order quantity: 5000 pcs, 5000 pcs/bulk

Absolute Maximum Ratings

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Value	Unit
Collector emitter voltage		V_{CEO}	70	V
Emitter collector voltage		V_{ECO}	5	V
Collector current		I_C	50	mA
Collector peak current	$t_p/T = 0.5, t_p \leq 10$ ms	I_{CM}	100	mA
Power dissipation	$T_{amb} \leq 55$ °C	P_V	100	mW
Junction temperature		T_j	100	°C
Ambient temperature range		T_{amb}	- 40 to + 100	°C
Storage temperature range		T_{stg}	- 40 to + 100	°C
Soldering temperature	t ≤ 3 s, 2 mm from case	T_{sd}	260	°C
Thermal resistance junction/ ambient		R_{thJA}	450	K/W

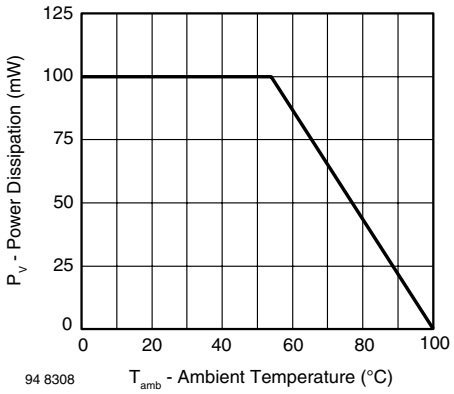


Figure 1. Power Dissipation Limit vs. Ambient Temperature

Basic Characteristics

T_{amb} = 25 °C, unless otherwise specified

Parameter	Test condition	Symbol	Min	Typ.	Max	Unit
Collector emitter breakdown voltage	I_C = 1 mA	$V_{(BR)CEO}$	70			V
Collector emitter dark current	V_{CE} = 20 V, E = 0	I_{CEO}		1	200	nA
Collector emitter capacitance	V_{CE} = 5 V, f = 1 MHz, E = 0	C_{CEO}		3		pF
Angle of half sensitivity		φ		± 25		deg
Wavelength of peak sensitivity		λ_p		850		nm
Range of spectral bandwidth		$\lambda_{0.5}$		620 to 980		nm
Collector emitter saturation voltage	E_e = 1 mW/cm^2, λ = 950 nm, I_C = 0.1 mA	V_{CEsat}			0.3	V
Turn-on time	V_S = 5 V, I_C = 5 mA, R_L = 100 Ω	t_{on}		2.0		µs
Turn-off time	V_S = 5 V, I_C = 5 mA, R_L = 100 Ω	t_{off}		2.3		µs
Cut-off frequency	V_S = 5 V, I_C = 5 mA, R_L = 100 Ω	f_c		180		kHz

Type Dedicated Characteristics

Parameter	Test condition	Part	Symbol	Min	Typ.	Max	Unit
Collector light current	E_e = 1 mW/cm^2, λ = 950 nm, V_{CE} = 5 V	BPW85A	I_{ca}	0.8	1.5	2.5	mA
		BPW85B	I_{ca}	1.5	2.5	4.0	mA
		BPW85C	I_{ca}	3.0	5.0	8.0	mA

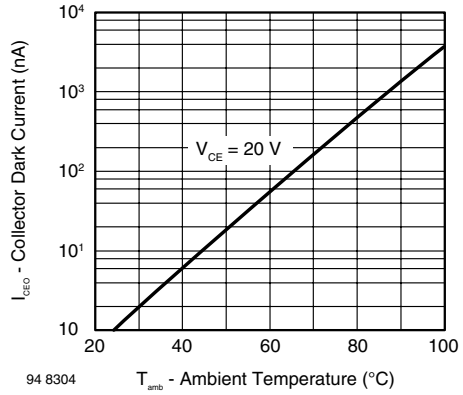


Figure 2. Collector Dark Current vs. Ambient Temperature

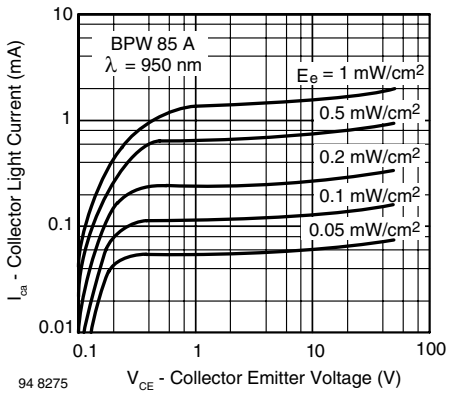


Figure 5. Collector Light Current vs. Collector Emitter Voltage

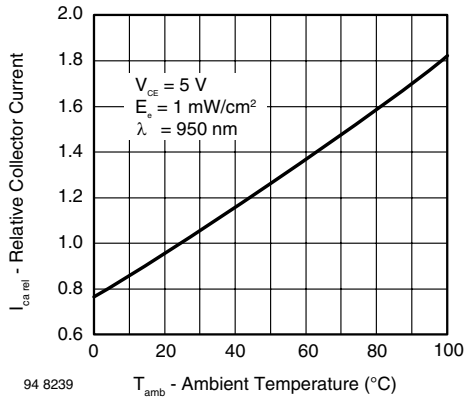


Figure 3. Relative Collector Current vs. Ambient Temperature

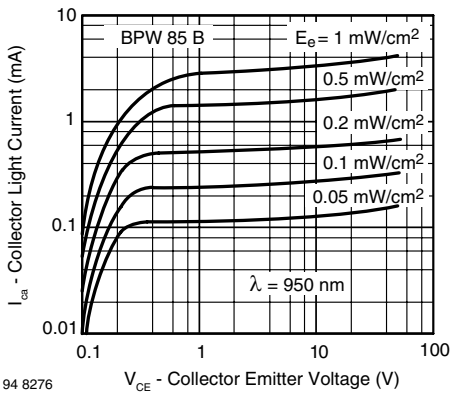


Figure 6. Collector Light Current vs. Collector Emitter Voltage

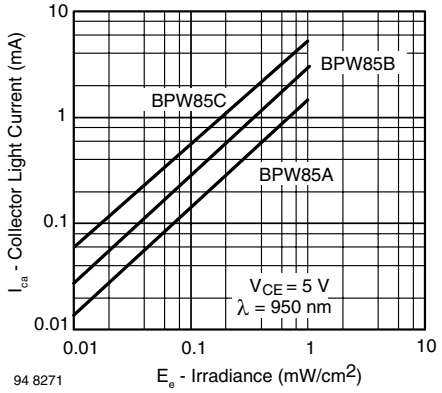


Figure 4. Collector Light Current vs. Irradiance

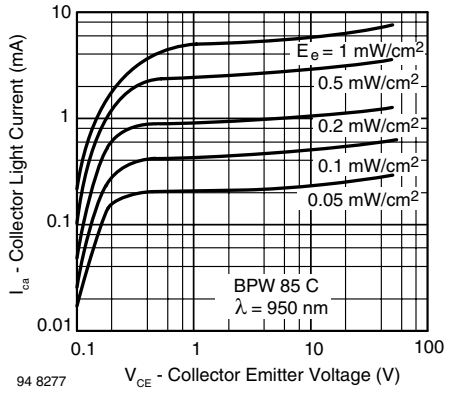


Figure 7. Collector Light Current vs. Collector Emitter Voltage

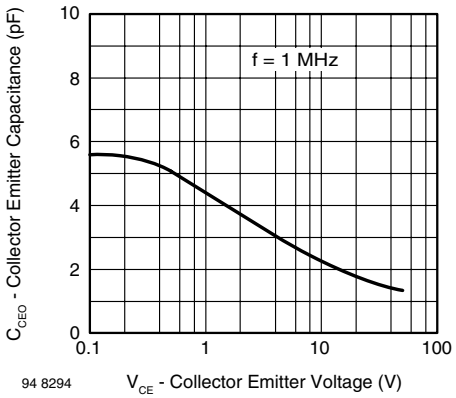


Figure 8. Collector Emitter Capacitance vs. Collector Emitter Voltage

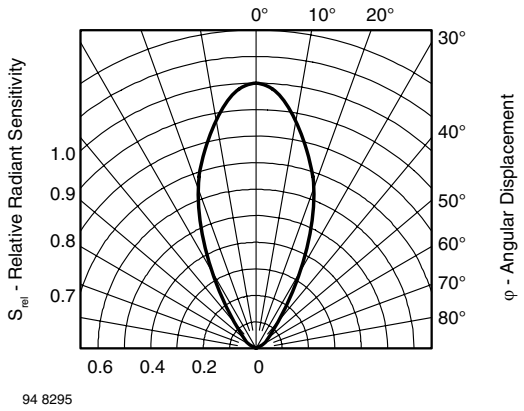


Figure 11. Relative Radiant Sensitivity vs. Angular Displacement

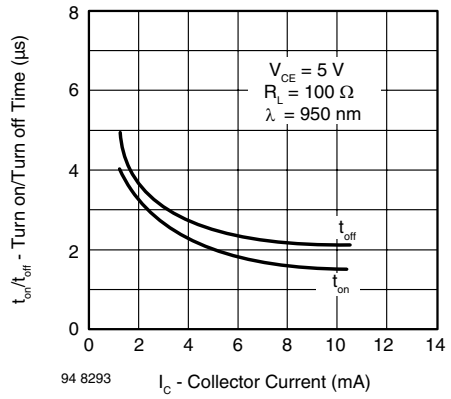


Figure 9. Turn-on/Turn-off Time vs. Collector Current

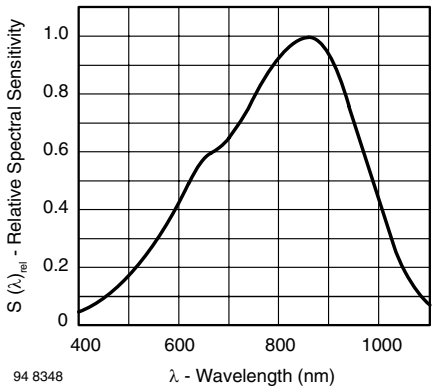
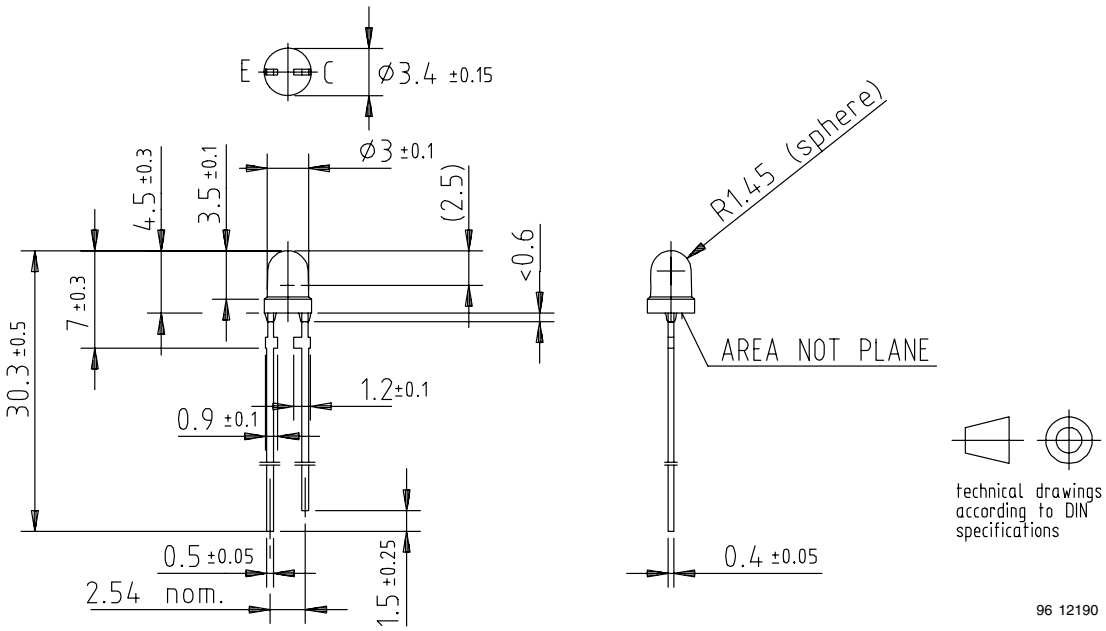


Figure 10. Relative Spectral Sensitivity vs. Wavelength

Package Dimensions in millimeters



Ozone Depleting Substances Policy Statement

It is the policy of Vishay Semiconductor GmbH to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

Vishay Semiconductor GmbH, P.O.B. 3535, D-74025 Heilbronn, Germany

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